

**Amendments to the Specification:**

Amend the paragraph on page 11, beginning on line 18, as follows:

-- Figure 4 diagrammatically illustrates a longitudinal section through the optically pumped semiconductor device illustrated in Figure 2 along the resonator axis B-B. The vertical emitter 13 comprises a quantum well structure 7 spaced from a mirror structure 14, said mirror structure preferably being formed as a Bragg mirror. Each one of structures 7 and 14 can be arranged above or below the other, and additional layers can be arranged therebetween. The radiation 12 generated by the vertical emitter is radiated through the substrate 8. Preferably, an external mirror ~~15~~ 25 may be provided in order to form a VECSEL (Vertical External Cavity Surface Emitting Laser). --

Amend the paragraph on page 12, beginning on line 6, as follows:

-- The centrally formed vertical emitter 13 is adjoined laterally in each case by a region of the pump laser 16. The pump laser 16 comprises an active layer 9 arranged between a first waveguide layer 18 and a second waveguide layer 19, the two waveguide layers 18 and 19 forming a waveguide for the pump laser 16 in the vertical direction. Said waveguide is in turn arranged between two cladding layers 15 and ~~16~~ 23 spaced from each other. Each one of layers 15 and ~~16~~ 23 can be arranged above or below the other, and additional layers can be arranged therebetween. --